# TPMV50XNEAR

## 30V N-Channel Power MOSFET



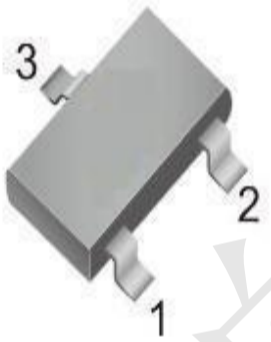
### Key Parameter Performance

| Parameter | | Value | Unit |
|---|---|---|---|
| $V_{DS}$ | | 30 | V |
| $R_{DS(on)}$ (max) | $V_{GS}$ = 10V | 24 | mΩ |
| | $V_{GS}$ = 4.5V | 34 | |
| $Q_g$ | | 4.1 | nC |

**Pin Definition:**
1. Gate
2. Source
3. Drain

**Note:**
MSL 1 (Moisture Sensitivity Level) per J-STD-020

## Block Diagram

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N-Channel MOSFET

### Absolute Maximum Ratings ($T_C$ = 25°C unless otherwise noted)

| Parameter | | Symbol | Limit | Unit |
|---|---|---|---|---|
| Drain-Source Voltage | | $V_{DS}$ | 30 | V |
| Gate-Source Voltage | | $V_{GS}$ | ±20 | V |
| Continuous Drain Current | $T_C$ = 25°C | $I_D$ | 6.5 | A |
| | $T_C$ = 100°C | | 4.1 | A |
| Pulsed Drain Current (Note 1) | | $I_{DM}$ | 26 | A |
| Single Pulse Avalanche Energy (Note 2) | | $E_{AS}$ | 32 | mJ |
| Power Dissipation @ $T_C$ = 25°C | | $P_D$ | 1.56 | W |
| Operating Junction Temperature | | $T_J$ | -55 to +150 | °C |
| Storage Temperature Range | | $T_{STG}$ | -55 to +150 | °C |

### Thermal Performance

| Parameter | Symbol | Limit | Unit |
|---|---|---|---|
| Thermal Resistance - Junction to Ambient | $R_{\Theta JA}$ | 80 | °C/W |

## Electrical Specifications ($T_C$ = 25°C unless otherwise noted)

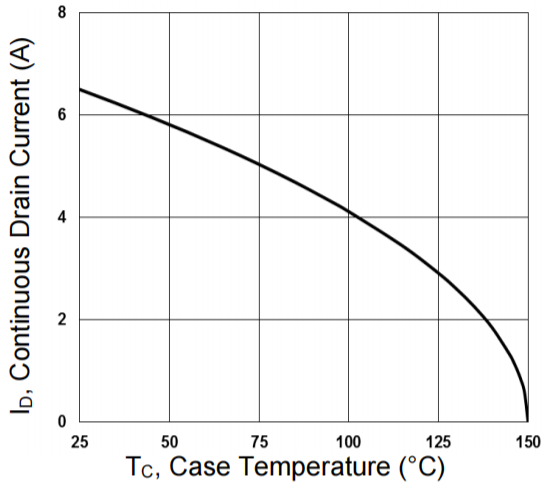
| Parameter | Conditions | Symbol | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| **Static** | | | | | | |
| Drain-Source Breakdown Voltage | $V_{GS}$ = 0V, $I_D$ = 250μA | $BV_{DSS}$ | 30 | -- | -- | V |
| Drain-Source On-State Resistance | $V_{GS}$ = 10V, $I_D$ = 6A | $R_{DS(on)}$ | -- | 17 | 24 | mΩ |
| | $V_{GS}$ = 4.5V, $I_D$ = 4A | | -- | 22 | 34 | |
| Gate Threshold Voltage | $V_{DS}$ = $V_{GS}$, $I_D$ = 250μA | $V_{GS(TH)}$ | 1.2 | 1.4 | 2.5 | V |
| Zero Gate Voltage Drain Current | $V_{DS}$ = 30V, $V_{GS}$ = 0V | $I_{DSS}$ | -- | -- | 1 | μA |
| | $V_{DS}$ = 24V, $T_J$ = 125°C | | -- | -- | 10 | |
| Gate Body Leakage | $V_{GS}$ = ±20V, $V_{DS}$ = 0V | $I_{GSS}$ | -- | -- | ±100 | μA |
| Forward Transconductance (Note 3) | $V_{DS}$ = 10V, $I_D$ = 4A | $g_{fs}$ | -- | 6.5 | -- | S |
| **Dynamic** | | | | | | |
| Total Gate Charge (Note 3,4) | $V_{DS}$ = 15V, $I_D$ = 6A, $V_{GS}$ = 4.5V | $Q_g$ | -- | 4.1 | -- | nC |
| Gate-Source Charge (Note 3,4) | | $Q_{gs}$ | -- | 1 | -- | |
| Gate-Drain Charge (Note 3,4) | | $Q_{gd}$ | -- | 2.1 | -- | |
| Input Capacitance | $V_{DS}$ = 25V, $V_{GS}$ = 0V, f = 1.0MHz | $C_{iss}$ | -- | 345 | -- | pF |
| Output Capacitance | | $C_{oss}$ | -- | 55 | -- | |
| Reverse Transfer Capacitance | | $C_{rss}$ | -- | 32 | -- | |
| **Switching** | | | | | | |
| Turn-On Delay Time (Note 3,4) | $V_{DD}$ = 15V, $I_D$ = 1A, $V_{GS}$ = 10V, $R_G$ = 6Ω | $t_{d(on)}$ | -- | 2.8 | -- | ns |
| Turn-On Rise Time (Note 3,4) | | $t_r$ | -- | 7.2 | -- | |
| Turn-Off Delay Time (Note 3,4) | | $t_{d(off)}$ | -- | 15.8 | -- | |
| Turn-Off Fall Time (Note 3,4) | | $t_f$ | -- | 4.6 | -- | |
| **Source-Drain Diode Ratings and Characteristic** | | | | | | |
| Maximum Continuous Drain-Source Diode Forward Current | Integral reverse diode in the MOSFET | $I_S$ | -- | -- | 6.5 | A |
| Maximum Pulse Drain-Source Diode Forward Current | | $I_{SM}$ | -- | -- | 26 | A |
| Diode-Source Forward Voltage | $V_{GS}$ = 0V, $I_S$ = 1A | $V_{SD}$ | -- | -- | 1 | V |

**Note:**

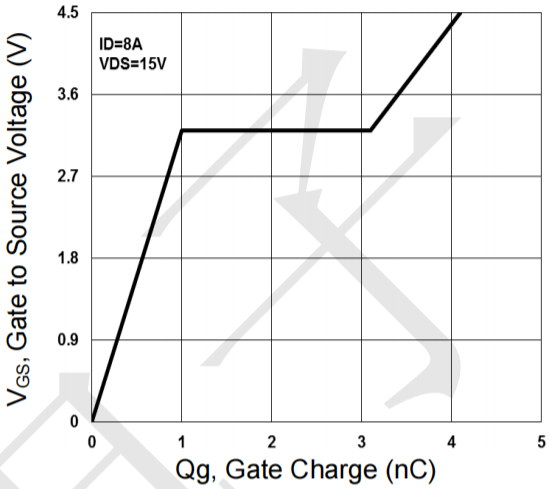
1. Pulse width limited by safe operating area
2. L = 1mH, $I_{AS}$ = 8A, $V_{DD}$ = 25V, $R_G$ = 25Ω, Starting $T_J$ = 25°C
3. Pulse test: pulse width ≤ 300μs, duty cycle ≤ 2%
4. Switching time is essentially independent of operating temperature.

## Electrical Characteristics Curve

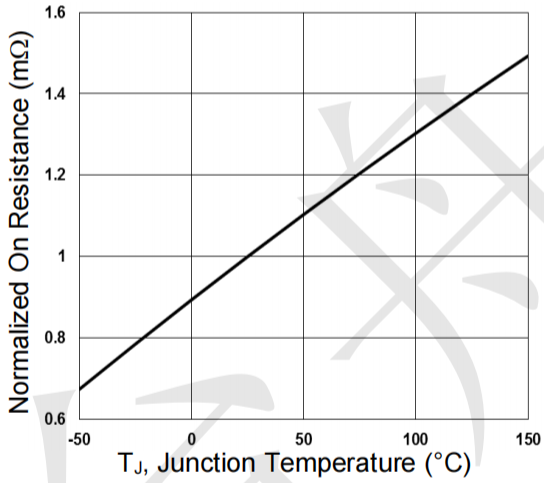
### Continuous Drain Current vs. $T_C$



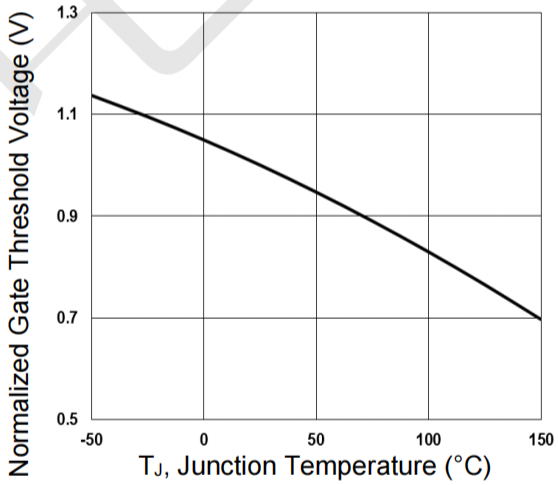

### Gate Charge



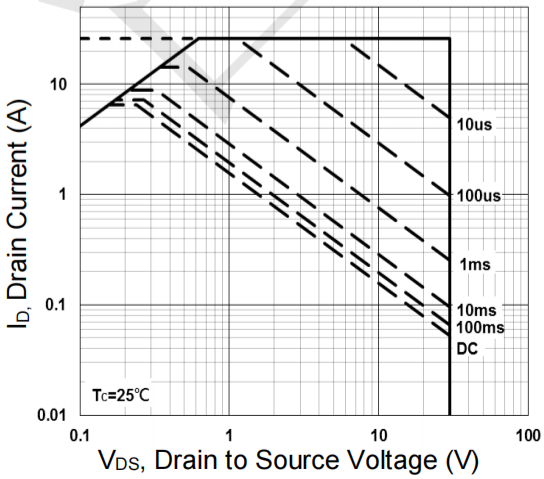

### On-Resistance vs. Junction Temperature



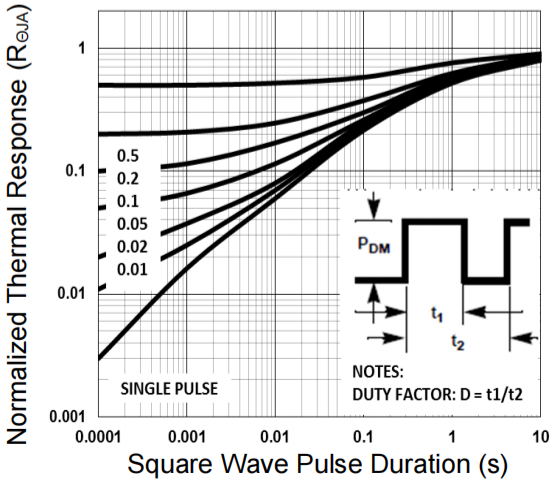

### Threshold Voltage vs. Junction Temperature




### Maximum Safe Operating Area




### Normalized Thermal Transient Impedance Curve



## Package information (Unit: mm)

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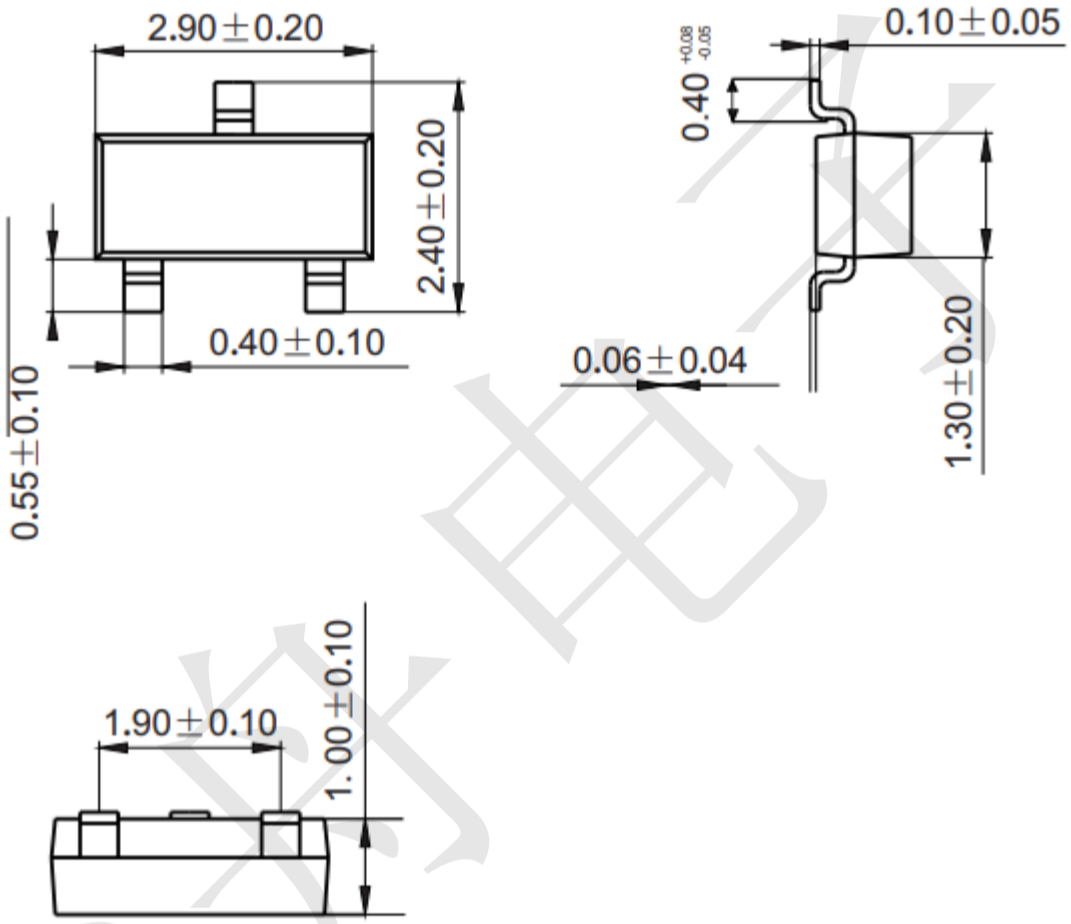


## Mounting Pad Layout (Unit: mm)